UNITED STATES PATENT AND TRADEMARK OFFICE **CERTIFICATE OF CORRECTION**

PATENT NO.

: 6,921,692 B2

DATED

: July 26, 2005

INVENTOR(S): Kunal R. Parekh et al.

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Title page,

Item [56], References Cited, U.S. PATENT DOCUMENTS,

delete "6,458, 859 B2 10/2002

Hayashida et al." and insert

Page 1 of 2

-- 6,468,859 B2 10/2002

Hayashida et al. --.

Column 4,

Line 36, replace "of example only, layer 54 might be formed to to provide a" with

-- of example only, layer 54 might be formed to provide a --.

Line 40, replace "layer 54 include conductive metal suicides (whether" with

-- layer 54 include conductive metal silicides (whether --.

Column 7,

Line 17, replace "The method of claim 13 wherein the sacrificial" with

-- The method of claim 17 wherein the sacrificial --.

Line 60, replace "plugging material with in the bit node contact opening"

with -- plugging materal within the bit mode contact opening --.

Line 66, replace "The method of claim 23 wherein the forming or the" with

-- The method of claim 23 wherein the forming of the --.

Column 9,

Line 52, replace "plagiarizing sacrificial plugging material." with

-- planarizing sacrificial plugging material. --.

Column 10,

Line 13, replace "plagiarizing sacrificial plugging material."

with -- planarizing sacrificial plugging material. --.

Line 27, replace "outer material Selectively to the etch stop material."

with -- outer material selectively to the etch stop material. --.

Line 47, replace "plagiarizing sacrifical plugging material."

with -- planarizing sacrificial plugging material. --.

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Column 10, (cont'd),

Line 53, replace "node, the capacitor node, the first node, arid the second node." with -- node, the capacitor node, the first node, and the second node. --.

Signed and Sealed this

Twenty-third Day of May, 2006

JON W. DUDAS Director of the United States Patent and Trademark Office